



60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _{D Max} Tc = +25°C	
60V	$10.5 \text{m}\Omega @ V_{GS} = 10V$	75A	
	$15m\Omega @ V_{GS} = 4.5V$	62A	

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Backlighting

Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low On-Resistance
- Low Input Capacitance
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: TO251
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)

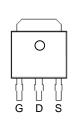




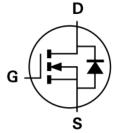




Bottom View



Top View Pin Configuration



Internal Schematic

Ordering Information (Note 4)

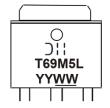
Part Number	Case	Packaging	
DMT69M5LH3	TO251 (Type TH3)	75 Pieces / Tube	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information

TO251 (Type TH3)



☐ H = Manufacturer's Marking
T69M5L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 20 = 2020)
WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	T _C = +25°C T _C = +70°C	lo	75 60	А
Maximum Body Diode Forward Current (Note 6)	Is	75	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	300	Α	
Pulsed Body Diode Current (10µs Pulse, Duty Cycle = 1%)	lsм	300	Α	
Avalanche Current, L = 0.1mH	las	27.4	Α	
Avalanche Energy, L = 0.1mH	Eas	37.5	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	3.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	38	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	PD	96	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	1.3	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						rest condition	
Drain-Source Breakdown Voltage	BVpss	60	_	_	V	$V_{GS} = 0V, I_{D} = 250 \mu A$	
Zero Gate Voltage Drain Current	Ipss	_	_	1	μΑ	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)					ı	1 22	
Gate Threshold Voltage	V _G S(TH)	1.4	_	2.5	V	V _{DS} = V _{GS} , I _D = 250μA	
Static Drain-Source On-Resistance	D	_	5.8	10.5	mΩ	Vgs = 10V, ID = 20A	
Static Drain-Source On-Resistance	RDS(ON)	_	8.5	15	11122	V _G S = 4.5V, I _D = 20A	
Diode Forward Voltage	V _{SD}	_	8.0	1.2	V	V _{GS} = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 8)					•		
Input Capacitance	Ciss	_	1406	_	pF	.,	
Output Capacitance	Coss	_	540	_	pF	V _{DS} = 30V, V _{GS} = 0V, - f = 1MHz	
Reverse Transfer Capacitance	Crss	_	52	_	pF	1 = 1101112	
Gate Resistance	Rg	_	1.85	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (VGS = 10V)	Qg	_	28.4	_	nC		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	15.4	_	nC	7, 20, 1, 40, 54	
Gate-Source Charge	Qgs	_	2.4	_	nC	$V_{DS} = 30V, I_{D} = 13.5A$	
Gate-Drain Charge	Qgd	_	9.0	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	10.5	_	ns		
Turn-On Rise Time	t _R	_	49.0	_	ns	V _{DD} = 30V, V _{GS} = 10V,	
Turn-Off Delay Time	t _{D(OFF)}	_	30.9	_	ns	$R_G = 6\Omega$, $I_D = 13.5A$	
Turn-Off Fall Time	tF	_	79.5	_	ns		
Body Diode Reverse Recovery Time	trr	_	26.7	_	ns	10.54 11/11 0004/	
Body Diode Reverse Recovery Charge	QRR	_	44.8	_	nC	$I_F = 13.5A$, di/dt = 300A/ μ s	

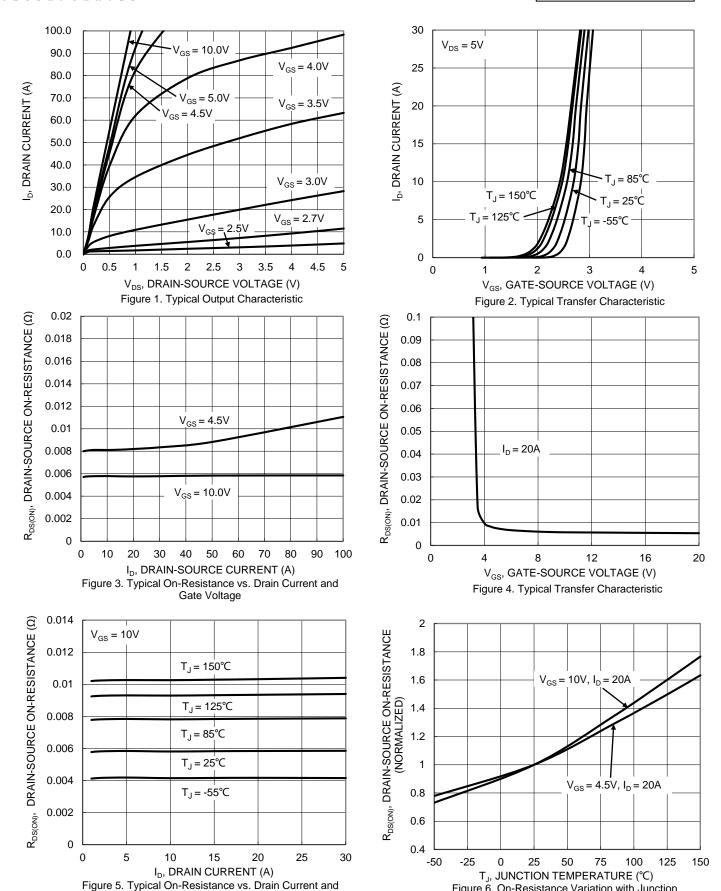
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

^{6.} Device mounted on infinite heatsink.

^{7.} Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to production testing.





Junction Temperature

Figure 6. On-Resistance Variation with Junction

Temperature



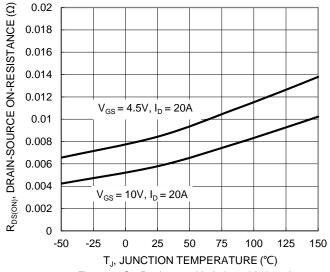
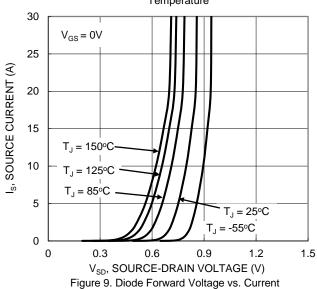
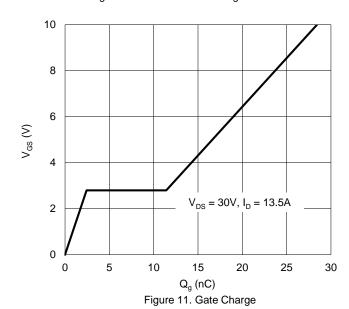
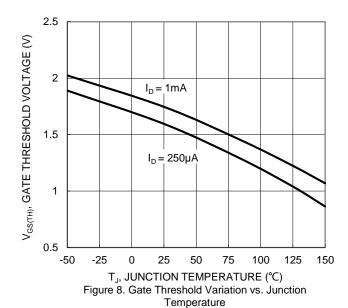
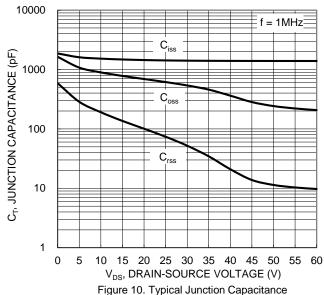


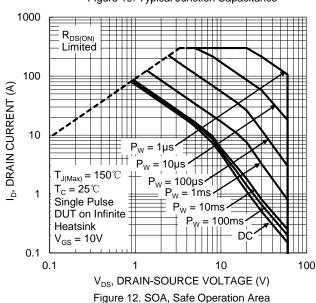
Figure 7. On-Resistance Variation with Junction Temperature













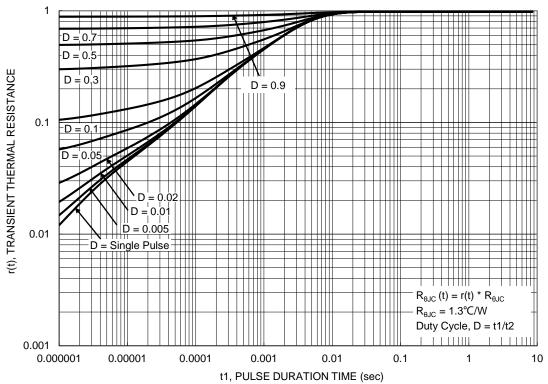


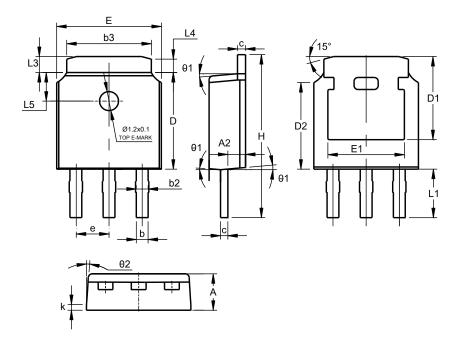
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO251 (Type TH3)



TO251 (Type TH3)					
Dim	Min	Тур			
Α	2.20	2.40	2.30		
A2	0.97	1.17	1.07		
b	0.68	0.90	0.78		
b2	0.76	0.95	0.84		
b3	5.20	5.50	5.33		
С	0.43	0.63	0.53		
D	5.98	5.98 6.22			
D1	5.30 REF				
D2	5.26	5.46			
е	2.286 BSC				
Е	6.40	6.80	6.60		
E1	4.63	5.03	4.83		
Н	9.40	9.85	9.62		
k	0.40REF				
L1	2.30	2.70	2.50		
L3	0.88 1.28		1.02		
L4	0.75 REF				
L5	1.65	1.95	1.80		
θ1	5°	9°	7°		
θ2	5° 9° 7°				
All Dimensions in mm					



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